



# LOW POWER NPN SILICON TRANSISTOR

Qualified per MIL-PRF-19500/391

**Qualified Levels:** JAN, JANTX, JANTXV, and JANS

### **DESCRIPTION**

This 2N3019 NPN leaded silicon transistor device is military qualified for high-reliability applications. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

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#### **FEATURES**

- JEDEC registered 2N3019 number.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/391.
- Rad hard levels are also available per MIL-PRF-19500/391. (For RHA datasheet see JANSD2N3019.)
- RoHS compliant by design.

### **APPLICATIONS / BENEFITS**

- Long leaded TO-5 package.
- Lightweight.
- Low power.
- Military and other high-reliability applications.

TO-18 (TO-206AA)

(leaded) 2N3700

**TO-5 Package** 

Also available in:

TO-39 (TO-205AD)

TO-46 (TO-206AB)

(short-leaded) 2N3019S

> (leaded) 2N3057A

**UB** package (leaded) 2N3700UB

### MAXIMUM RATINGS @ T<sub>A</sub> = +25 °C unless otherwise noted

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T <sub>J</sub> and T <sub>STG</sub>	-65 to +200	°C
Thermal Resistance Junction-to-Ambient	R <sub>OJA</sub>	195	°C/W
Thermal Resistance Junction-to-Case	R <sub>eJC</sub>	30	°C/W
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Collector-Base Voltage	V <sub>CBO</sub>	140	V
Emitter-Base Voltage	V <sub>EBO</sub>	7.0	V
Collector Current	I <sub>C</sub>	1.0	Α
Total Power Dissipation: @ $T_A = +25$ °C (1)	P <sub>D</sub>	0.8	W
@ $T_C = +25$ °C <sup>(2)</sup>		5.0	

Notes:

- 1. Derate linearly 4.6 mW/°C for  $T_A \ge +25$  °C.
- 2. Derate linearly 28.6 mW/°C for T<sub>C</sub> ≥ +25 °C.

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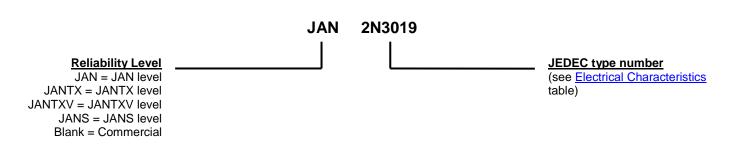
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## **MECHANICAL and PACKAGING**

- CASE: Hermetically sealed, kovar base, nickel cap.
- TERMINALS: Gold plate, solder dip (Sn63/Pb37) available upon request. NOTE: Solder dip will eliminate RoHS compliance.
- MARKING: Part number, date code, manufacturer's ID and serial number.
- POLARITY: NPN.
- WEIGHT: Approximately 1.064 grams.
- See Package Dimensions on last page.

## **PART NOMENCLATURE**



SYMBOLS & DEFINITIONS			
Symbol	Definition		
f	Frequency		
I <sub>B</sub>	Base current (dc)		
Ι <sub>Ε</sub>	Emitter current (dc)		
T <sub>A</sub>	Ambient temperature		
T <sub>C</sub>	Case temperature		
$V_{CB}$	Collector to base voltage (dc)		
V <sub>CE</sub>	Collector to emitter voltage (dc)		
$V_{EB}$	Emitter to base voltage (dc)		



# **ELECTRICAL CHARACTERISTICS** @ T<sub>A</sub> = +25 °C, unless otherwise noted

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Current $I_C = 30 \text{ mA}$	V <sub>(BR)CEO</sub>	80		V
Collector-Base Cutoff Current V <sub>CB</sub> = 140 V	I <sub>CBO</sub>		10	μA
Emitter-Base Cutoff Current $V_{EB} = 7 \text{ V}$	I <sub>EBO1</sub>		10	μA
Collector-Emitter Cutoff Current V <sub>CE</sub> = 90 V	I <sub>CES</sub>		10	ηΑ
Emitter-Base Cutoff Current V <sub>EB</sub> = 5.0 V	I <sub>EBO2</sub>		10	ηΑ
ON CHARACTERISTICS				
Forward-Current Transfer Ratio				
$I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$		100	300	
$I_C = 0.1 \text{ mA}, V_{CE} = 10 \text{ V}$		50	300	
$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	h <sub>FE</sub>	90		
$I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}$		50	300	
$I_C = 1.0 \text{ A}, V_{CE} = 10 \text{ V}$		15		
Collector-Emitter Saturation Voltage				
$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	V <sub>CE(sat)</sub>		0.2 0.5	V
Base-Emitter Saturation Voltage				
$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	$V_{BE(sat)}$		1.1	V

## **DYNAMIC CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 1.0$ mA, $V_{CE} = 5.0$ V, $f = 1.0$ kHz	h <sub>fe</sub>	80	400	
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 50 \text{ mA}, \ V_{CE} = 10 \text{ V}, \ f = 20 \text{ MHz}$	h <sub>fe</sub>	5.0	20	
Output Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$	C <sub>obo</sub>		12	pF
Input Capacitance $V_{EB} = 0.5 \text{ V}, I_C = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$	C <sub>ibo</sub>		60	pF

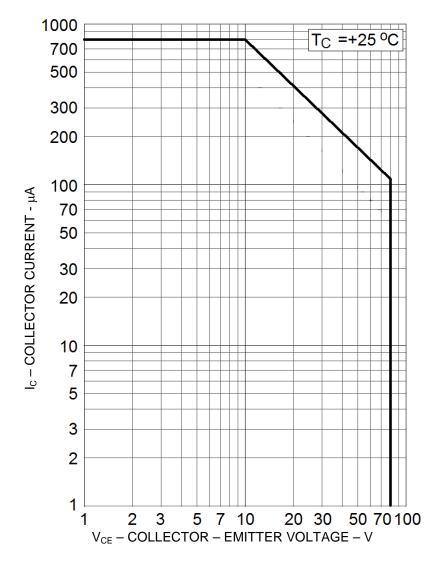


## **ELECTRICAL CHARACTERISTICS** @ T<sub>A</sub> = +25 °C, unless otherwise noted (continued)

## SAFE OPERATION AREA (See SOA graph below and MIL-STD-750, method 3053)

DC Tests T <sub>C</sub> = 25 °C, 1 cycle, t = 10 ms	
Test 1	$V_{CE} = 10 \text{ V}$ $I_{C} = 500 \text{ mA}$
Test 2	$V_{CE} = 40 \text{ V}$ $I_C = 125 \text{ mA}$
Test 3	$V_{CE} = 80 \text{ V}$ $I_C = 60 \text{ mA}$

(1) Pulse Test: Pulse Width = 300  $\mu$ s, duty cycle  $\leq$  2.0%.



Maximum Safe Operating Area



## **GRAPHS**

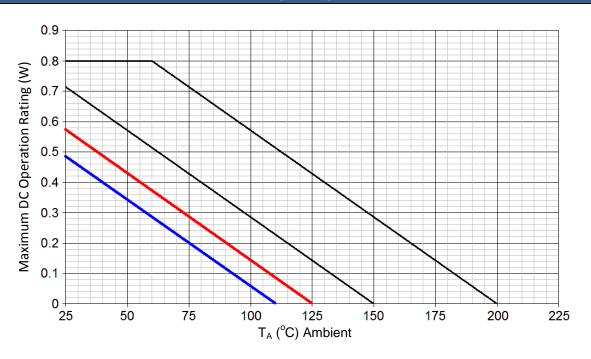


FIGURE 1
Temperature – Power Derating (R<sub>eJA</sub>)

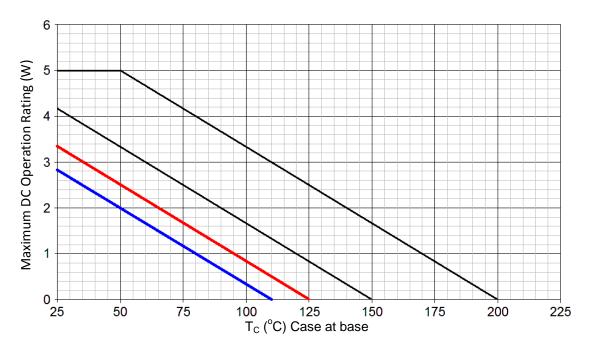
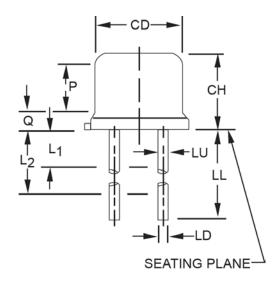


FIGURE 2

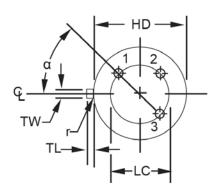
<u>Temperature – Power Derating (Rejc)</u>



## **PACKAGE DIMENSIONS**



	Dimensions				
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	
CH	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200 TP		5.08 TP		6
LD	.016	.021	0.41	0.53	7, 8
LL	1.500	1.750	38.10	44.45	7, 8
LU	.016	.019	0.41	0.48	7, 8
L <sub>1</sub>		.050		1.27	7, 8
L <sub>2</sub>	.250		6.35		7, 8
Q		.050		1.27	5
TL	.029	.045	0.74	1.14	4
TW	.028	.034	0.71	0.86	3
r		.010		0.25	10
α	45° TP		45° TP		6
Р	.100	-	2.54	-	



### **NOTES:**

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- 4. Dimension TL measured from maximum HD.
- 5. Body contour optional within zone defined by HD, CD, and Q.
- 6. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. This device may be measured by direct methods.
- 7. Dimension LU applies between L1 and L2. Dimension LD applies between L2 and minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
- 8. All three leads.
- 9. The collector shall be internally connected to the case.
- 10. Dimension r (radius) applies to both inside corners of tab.
- 11. In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi x$  symbology.
- 12. Lead 1 = emitter, lead 2 = base, lead 3 = collector.

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